Product data sheet

1. General description

Ultrafast power diode in a TO247-2L plastic package.

2. Features and benefits

- Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- Low leakage current
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT
- High operating temperature capability $(T_{j \text{ (max)}} = 175^{\circ}\text{C})$

3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter Conditions			Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 129$ °C; Fig. 1; Fig. 2; Fig. 3	60			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; T_{mb} ≤ 129 °C; square-wave pulse	120			А	
I _{FSM} non-repetitive peak forward current		t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600		А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	660		А		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.2	1.6	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	55	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K 14 A
2	А	anode		K A 001aaa020
mb	mb	mounting base; connected to cathode	K A TO247-2L	

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYQ60W-600PT2	TO247-2L	BYQ60W-600PT2Q	Tube	30	TO247L-2L	10-Nov-2020

7. Marking

Table 4. Marking codes

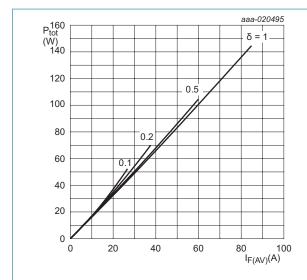
Type number	Marking codes
BYQ60W-600PT2	BYQ60W 600PT2

8. Limiting values

Table 5. Limiting values

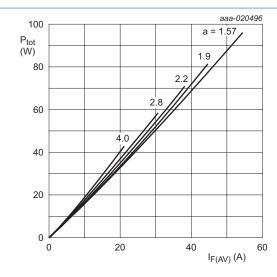
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 129$ °C; Fig. 1; Fig. 2; Fig. 3	60	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 129 °C$; square-wave pulse	120	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	660	А
l ² t	limiting Joule-integral	SIN; t _p = 10 ms	1800	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



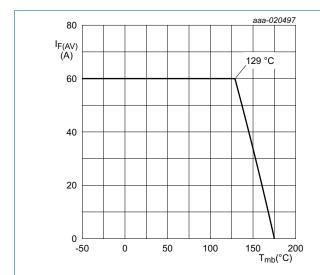
 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 1.600 \text{ V; } R_s = 0.0013 \text{ }\Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.600 V; R_s = 0.0013 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





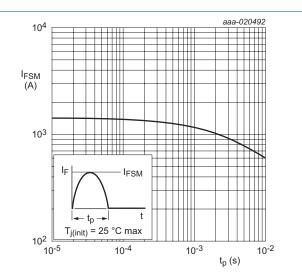


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.44	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

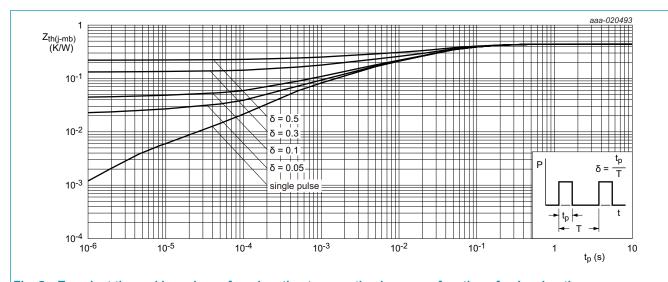
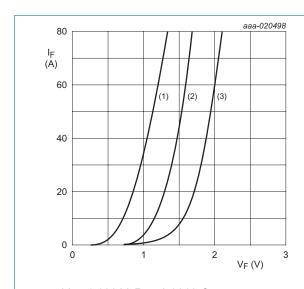


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V_{F}	forward current	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 125 °C	-	-	500	μΑ
Dynamic	characteristics		,			
Q _r	reverse charge	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	143	-	nC
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	876	-	nC
t _{rr} I	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	55	ns
		$I_F = 60 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_J = 25 \text{ °C}$; Fig. 7	-	53	-	ns
		$I_F = 60 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_J = 125 \text{ °C}$; Fig. 7	-	120	-	ns
I _{RM}	peak reverse recovery current	$I_F = 60 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/µs}$; $T_j = 25 \text{ °C}$; Fig. 7	-	5.4	-	А
		$I_F = 60 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_i = 125 \text{ °C}$; $Fig. 7$	-	14.5	-	Α



 $V_o = 1.600 \text{ V}; R_s = 0.0013 \Omega$

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage

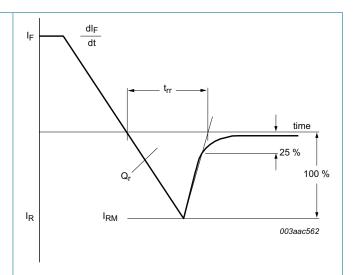
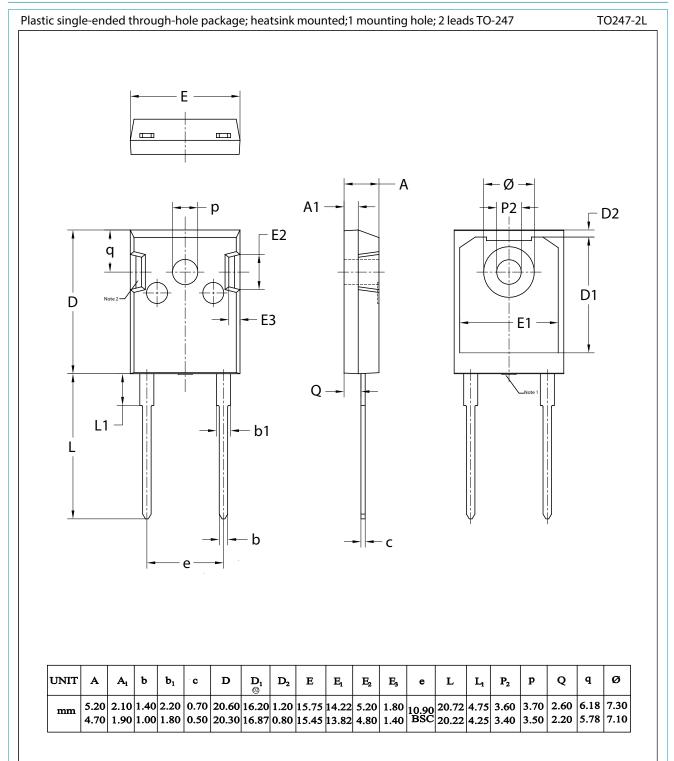


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Note:

Mold resin protrusion max 0.127mm. Metal exposed with Sn plating.

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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